Time		Coherence	Qubit	Material	Host	Date	Reference	Source
57	s	T_1	LD/e	GaAs/AlGaAs	2D	2018-08	1	p3 and Fig. 4a
30	s	T_1	LD/i	Si:P	imp	2017-03	2	Fig. 2b the lowest point
10	s	T_1	LD/e	GaAs/AlGaAs	2D	2017-10	3	Fig. 2 the lowest green point
9.8	s	T_1	LD/i	Si:P	imp	2019-05	4	Fig. 2c
9.3	s	T_1	LD/i	Si:P	imp	2018-03	5	p3 and Fig. 1f
9	s	T_1	LD/e	Si/SiO_2	1D	2021-03	6	p3 and Fig. 3a the leftmost blue point
6	s	T_1	LD/i	Si:P	imp	2010-09	7	p2
5	s[a]	T_1	LD/e	Si/SiGe	2D	2019-04	8	p4
4.2	s	T_1	LD/i	Si:P	imp	2019-01	9	p3
3.4	s	T_1	LD/i	^{28}Si:P	imp	2021-01	10	p6 and SFig. 3c
3	s	T_1	LD/i	^{28}Si:P	imp	2016-10	11	p3
3	s	T_1	ST/e	Si/SiGe	2D	2012-01	12	p4
2.8	s	T_1	LD/e	Si/SiGe	2D	2011-04	13	p3 and Fig. 3
2.6	s	T_1	LD/e	Si/SiO_2	2D	2013-06	14	p3
1.8	s	T_1	LD/i	Si:P	imp	2013-06	15	Fig. 3
1.6	s	T_1	LD/e	$^{28}Si/SiO_2$	2D	2022-03	16	p4 and Fig. 3c
1.3	s	T_1	LD/i[b]	^{28}Si:P	imp	2016-10	17	p4
1.3	s	T_1	LD/i	Si:P	imp	2018-11	18	p3 and Fig. 2b
1	s	T_1	LD/e	GaAs/AlGaAs	2D	2008-01	19	p4 and Fig. 3c the leftmost blue point
1	s	T_1	LD/e	$^{28}Si/SiO_2$	2D	2018-10	20	p2
1	s	T_1	LD/e	^{28}Si/SiGe	2D	2020-03	21	p6 and Fig. 4a
0.7	s	T_1	LD/i	Si:P	imp	2012-09	22	p3
0.6	s[c]	T_1	LD/e	Si/SiGe	2D	2009-08	23	Fig. 5
0.5	s[d]	T_1	ST/e	$^{28}Si/SiO_2$	2D	2020-04	24	Fig. 4 the leftmost black point
0.17	s	T_1	LD/e	Si/SiGe	2D	2016-11	25	Fig. 6
0.16	s[e]	T_1	LD/e	Si/SiGe	2D	2019-04	8	Fig. 2
0.15	s[f]	T_1	LD/e	$^{28}Si/SiO_2$	2D	2018-08	26	p2 and p4
0.14	s	T_1	ST/e	Si/SiGe	2D	2012-04	27	Fig. 2d
0.13	s	T_1	LD/e	^{28}Si/SiGe	2D	2019-11	28	p4
90	ms	T_1	LD/e	Si/SiO_2	2D	2020-06	29	Fig. 1c
85	ms	T_1	LD/e	GaAs/AlGaAs	2D	2014-12	30	p2 and Fig. 3
50	ms	T_1	LD/e	Si/SiGe	2D	2018-02	31	p1 and ED Fig. 3b
40	ms	T_1	LD/e	Si/SiO_2	2D	2010-03	32	p4 and Fig. 4 the leftmost red point
32	ms	T_1	LD/h	Ge/SiGe	2D	2020-08	33	p3
32	ms	T_1	LD/e	^{28}Si/SiGe	2D	2022-12	34	p3
22	ms[g]	T_1	LD/e	Si/SiGe	2D	2022-08	35	p2 and ED Fig. 4b-d
20	ms	T_1	HY/e[h]	^{28}Si/SiGe	2D	2021-12	36	p4
16	ms	T_1	LD/h	Ge/SiGe	2D	2021-03	37	Fig. S5 dot 3
15	ms[i]	T_1	ST/e	$^{28}Si/SiO_2$	2D	2020-04	24	Fig. 4 the rightmost black point
10	ms	T_1	LD/e	Si/SiO_2	1D	2021-09	38	p2 and Fig. 2a
8.4	ms	T_1	LD/h	BLG	2D	2022-05	39	p5 and Fig. 4
5	ms	T_1	LD/i	^{28}Si:B	imp	2020-07	40	p3 and Fig. 3b
5	ms[j]	T_1	ST/e	$^{28}Si/SiO_2$	2D	2021-01	41	p4 and Fig. 1d
4.1	ms	T_1	ST/i	Si:P	imp	2014-06	42	
3.7	ms	T_1	LD/e	GaAs/AlGaAs	2D	2016-07	43	p3 and Fig. 2
3.7	ms	T_1	LD/e[k]	$^{28}Si/SiO_2$	2D	2020-04	44	p2
3.1	ms	T_1	LD/i	^{28}Si:P	imp	2022-01	45	ED Fig. 3 first column
2.8	ms[l]	T_1	LD/e	$^{28}Si/SiO_2$	2D	2018-08	26	p4 and Fig. 3a
2.3	ms[m]	T_1	ST/e	GaAs/AlGaAs	2D	2007-03	46	p2
1.5	ms	T_1	LD/e	GaAs/AlGaAs	2D	2019-04	47	Fig. 2

TABLE I-1. Spin coherence times (part 1). Superscripts stand for the following. [a]: No micromagnet. [b]: Qubit defined in the rotating frame. [c]: *(estimated)* Fig. 5 the lowest point. [d]: At 0.04 kelvin. [e]: With micromagnet. [f]: At 0.1 kelvin. [g]: The average over the three qubits. [h]: EO qubit. [i]: At 1.5 kelvin. [j]: Lifetime of T_- state. [k]: At 1 kelvin. [l]: At 1.1 kelvin. [m]: Triplet-singlet relaxation in a single dot.

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